PD- 93924

International
IOR Rectifier

PROVISIONAL

SMPS MOSFET

IRFBA32N50K

HEXFET® Power MOSFET

Applications

- Telecom and Data-Com off-Line SMPS
- UninterruptIble Power Supply

Benefits

- Low On-Resistance
- High Speed Switching
- Low Gate Drive Current Due to Improved Gate Charge Characteristics
- Improved Avalanche Ruggedness and Dynamic dv/dt, Fully Characterized Avalanche Voltage and Current

V_{DSS}	$R_{DS(on)}$	I_D
500V	**0.14Ω**	**32A**

Super-220™

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	32	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	20	
I_{DM}	Pulsed Drain Current ①	128	
P_D @T_C = 25°C	Power Dissipation	360	W
	Linear Derating Factor	2.9	W/°C
V_{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Recommended clip force	20	N

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	32	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	128		
V_{SD}	Diode Forward Voltage	——	——	1.5	V	T_J = 25°C, I_S = 32A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	——	650	——	ns	T_J = 125°C, I_F = 32A
Q_{rr}	Reverse RecoveryCharge	——	9.0	——	µC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Typical SMPS Topologies

- Hard Switching Full and Half Bridge Circuits
- Hard Switching Single Transistor Circuits
- Power Factor Correction Circuits

Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.55	—	V/°C	Reference to 25°C, I_D = 1mA⑥
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.14	Ω	V_{GS} = 10V, I_D = 19A ④
$V_{GS(th)}$	Gate Threshold Voltage	3.5	—	5.5	V	V_{DS} = V_{GS}, I_D = 250µA
I_{DSS}	Drain-to-Source Leakage Current	—	—	50	µA	V_{DS} = 500V, V_{GS} = 0V
		—	—	250	µA	V_{DS} = 400V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 30V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -30V

Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	12	—	—	S	V_{DS} = 50V, I_D = 19A
Q_g	Total Gate Charge	—	—	195	nC	I_D = 32A
Q_{gs}	Gate-to-Source Charge	—	—	75		V_{DS} = 400V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	90		V_{GS} = 10V, ④
$t_{d(on)}$	Turn-On Delay Time	—	20	—	ns	V_{DD} = 250V
t_r	Rise Time	—	60	—		I_D = 32A
$t_{d(off)}$	Turn-Off Delay Time	—	45	—		R_G = 4.3Ω
t_f	Fall Time	—	40	—		V_{GS} = 10V, ④
C_{iss}	Input Capacitance	—	5300	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	540	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	33	—		f = 1.0MHz

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	760	mJ
I_{AR}	Avalanche Current①	—	32	A
E_{AR}	Repetitive Avalanche Energy①	—	36	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.35	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	58	

Notes:

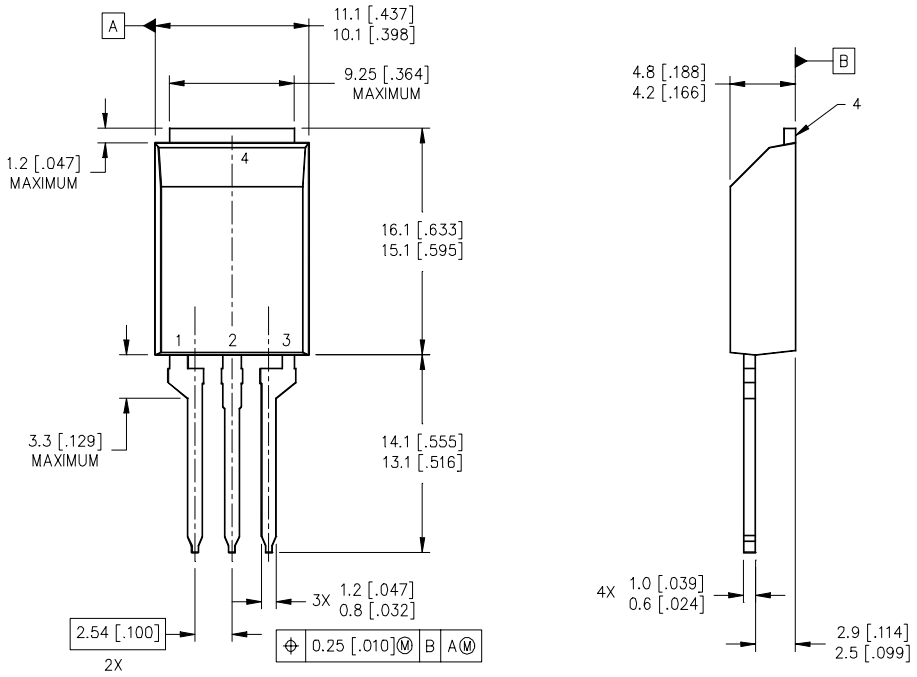
① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 4.3mH, R_G = 25Ω, I_{AS} = 32A,

③ I_{SD} ≤ 32A, di/dt ≤ TBDA/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150°C

④ Pulse width ≤ 400µs; duty cycle ≤ 2%.

Super-220™ Package Outline



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M–1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-273AA.

LEAD ASSIGNMENTS

MOSFET	IGBT
1 – GATE	1 – GATE
2 – DRAIN	2 – COLLECTOR
3 – SOURCE	3 – EMITTER
4 – DRAIN	4 – COLLECTOR

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Data and specifications subject to change without notice. 6/00